HiperFET ${ }^{\text {TM }}$
Power MOSFETs Q-Class

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode


| Symbol | Test Conditions | Maximum Ratings |  |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {DSs }}$ | $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$ | 1000 | V |
| $\mathrm{V}_{\text {DGR }}$ | $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}, \mathrm{R}_{\mathrm{GS}}=1 \mathrm{M} \Omega$ | 1000 | V |
| $V_{\text {GSs }}$ | Continuous | $\pm 20$ | V |
| $\mathrm{V}_{\text {GSM }}$ | Transient | $\pm 30$ | V |
| $\mathrm{I}_{\mathrm{D} 25}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | 4 | A |
| $\underline{\mathrm{I}_{\mathrm{DM}}}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$, Pulse Width Limited by $\mathrm{T}_{\text {JM }}$ | 16 | A |
| $\mathrm{I}_{\mathrm{A}}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | 4 | A |
| $\mathrm{E}_{\text {AS }}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | 700 | mJ |
| dv/dt | $\mathrm{I}_{\mathrm{s}} \leq \mathrm{I}_{\mathrm{DM}}, \mathrm{V}_{\mathrm{DD}} \leq \mathrm{V}_{\mathrm{DSS}}, \mathrm{T}_{\mathrm{J}} \leq 150^{\circ} \mathrm{C}$ | 5 | V/ns |
| $\mathrm{P}_{\mathrm{D}}$ | $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | 150 | W |
| $\mathrm{T}_{\mathrm{J}}$ |  | $-55 \ldots+150$ | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {JM }}$ |  | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ |  | $-55 \ldots+150$ | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Maximum Lead Temperature for Soldering | 300 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {soLD }}$ | Plastic Body for 10s | 260 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{M}_{\mathrm{c}}$ | Mounting Force (TO-263) | 10..65/2.2..14.6 | Nm/lb.in. |
| $\mathrm{M}_{\mathrm{d}}$ | Mounting Torque (TO-220) | 1.13/10 | Nm/lb.in. |
| Weight | TO-263 | 2.5 | g |
|  | TO-220 | 3.0 | g |


| Symbol Test Conditions <br> ( $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}$, Unless Otherwise Specified) |  |  | Characteristic Values |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min. | Typ. | Max. |
| $\mathrm{BV}_{\text {DSS }}$ | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1 \mathrm{~mA}$ |  | 1000 |  | V |
| $\mathrm{V}_{\mathrm{GS}(\mathrm{th})}$ | $\mathrm{V}_{\mathrm{DS}}=\mathrm{V}_{\mathrm{GS}}, \mathrm{I}_{\mathrm{D}}=1.5 \mathrm{~mA}$ |  | 2.5 |  | 4.5 V |
| $\mathrm{I}_{\text {GSS }}$ | $\mathrm{V}_{\mathrm{GS}}= \pm 20 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |  |  |  | $\pm 100 \mathrm{nA}$ |
| $\mathrm{I}_{\text {DSS }}$ | $\mathrm{V}_{\mathrm{DS}}=\mathrm{V}_{\mathrm{DSS}}, \mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}$ | $\mathrm{T}_{\mathrm{J}}=125^{\circ} \mathrm{C}$ |  |  | $\begin{array}{r} 50 \mu \mathrm{~A} \\ 1 \mathrm{~mA} \end{array}$ |
| $\mathrm{R}_{\text {DS(on) }}$ | $\mathrm{V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=0.5 \cdot \mathrm{I}_{\mathrm{D} 25}$ | Note 1 |  |  | 3.0 行 |

$$
\begin{aligned}
& \mathrm{V}_{\mathrm{Dss}}=1000 \mathrm{~V} \\
& \mathrm{I}_{\mathrm{D} 2 \mathrm{~s}}=4 \mathrm{~A} \\
& \mathrm{R}_{\mathrm{DS}(\text { (on })} \leq 3.0 \Omega
\end{aligned}
$$

TO-263 AA (IXFA)


TO-220AB (IXFP)


$$
\begin{array}{ll}
\mathrm{G}=\text { Gate } & \mathrm{D}=\text { Drain } \\
\mathrm{S}=\text { Source } & \text { Tab }=\text { Drain }
\end{array}
$$

## Features

- International Standard Packages
- Avalanche Rated
- Fast Intrinsic Diode
- Low $Q_{G}$
- Low $\mathrm{R}_{\mathrm{DS}(o n)}$
- Low Drain-to-Tab Capacitance
- Low Package Inductance


## Advantages

- High Power Density
- Easy to Mount
- Space Savings


## Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Temperature and Lighting Controls

IXFA4N100Q IXFP4N100Q

Symbol Test Conditions Characteristic Values

| ( $\mathrm{T}_{\mathrm{J}}=2$ | Unless Otherwise Specified) | Min. | Typ. | Max. |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{g}_{\text {fs }}$ | $\mathrm{V}_{\mathrm{DS}}=20 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=0.5 \cdot \mathrm{I}_{\mathrm{D} 25}$, Note 1 | 1.5 | 2.5 | S |
| $\begin{aligned} & \mathrm{C}_{\text {iss }} \\ & \mathrm{C}_{\text {oss }} \\ & \mathrm{C}_{\mathrm{rss}} \end{aligned}$ | $\} \mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=25 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |  | $\begin{array}{r} 1050 \\ 120 \\ 30 \end{array}$ | pF pF pF |
| $\begin{aligned} & t_{\mathrm{d}(\text { on })} \\ & \mathbf{t}_{\mathrm{r}} \\ & \mathbf{t}_{\mathrm{d}(\text { off })} \\ & t_{\mathrm{f}} \\ & \hline \end{aligned}$ | Resistive Switching Times $\left\{\begin{array}{l} \mathrm{V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0.5 \cdot \mathrm{~V}_{\mathrm{DSS}}, \mathrm{I}_{\mathrm{D}}=0.5 \cdot \mathrm{I}_{\mathrm{D} 25} \\ \mathrm{R}_{\mathrm{G}}=4.7 \Omega \text { (External) } \end{array}\right.$ |  | $\begin{aligned} & 17 \\ & 15 \\ & 32 \\ & 18 \end{aligned}$ | ns |
| $\begin{aligned} & \mathbf{Q}_{\mathrm{g}(o n)} \\ & \mathbf{Q}_{\mathrm{gs}} \\ & \mathbf{Q}_{\mathrm{gd}} \end{aligned}$ | \} $\mathrm{V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0.5 \cdot \mathrm{~V}_{\mathrm{DSS}}, \mathrm{I}_{\mathrm{D}}=0.5 \cdot \mathrm{I}_{\mathrm{D} 25}$ |  | $\begin{array}{r} 39 \\ 9 \\ 23 \end{array}$ | nC |
| $\mathrm{R}_{\mathrm{thJc}}$ <br> $\mathrm{R}_{\mathrm{thcs}}$ | TO-220 |  | 0.50 | $0.80^{\circ} \mathrm{C} / \mathrm{W}$ <br> ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## Source-Drain Diode

| Symbol Test Conditions$\left(T_{j}=25^{\circ} \mathrm{C}\right.$ Unless Otherwise Specified) |  | Characteristic Values |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min. | Typ. | Max. |  |
| $\mathrm{I}_{\mathrm{s}}$ | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}$ |  |  | 4 | A |
| $\mathrm{I}_{\mathrm{Sm}}$ | Repetitive, Pulse Width Limited by $\mathrm{T}_{\text {JM }}$ |  |  | 16 | A |
| $\mathrm{V}_{\text {sD }}$ | $\mathrm{I}_{\mathrm{F}}=\mathrm{I}_{\mathrm{S}}, \mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}$, Note 1 |  |  | 1.5 | V |
| $t_{r r}$ <br> $Q_{\text {RM }}$ <br> $\mathrm{I}_{\mathrm{RM}}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=\mathrm{I}_{\mathrm{S}},-\mathrm{di} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s} \\ & \mathrm{~V}_{\mathrm{R}}=100 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V} \end{aligned}$ |  | $\begin{gathered} 0.52 \\ 1.80 \end{gathered}$ | 250 | ns $\mu \mathrm{C}$ A |

Note

1. Pulse test, $\mathrm{t} \leq 300 \mu \mathrm{~s}$, duty cycle, $\mathrm{d} \leq 2 \%$.

TO-263 Outline


| SYM | INCHES |  | MLLLIMETERS |  |
| :--- | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | .160 | .190 | 4.06 | 4.83 |
| A1 | .080 | .110 | 2.03 | 2.79 |
| b | .020 | .039 | 0.51 | 0.99 |
| b2 | .045 | .055 | 1.14 | 1.40 |
| c | .016 | .029 | 0.40 | 0.74 |
| c2 | .045 | .055 | 1.14 | 1.40 |
| D | .340 | .380 | 8.64 | 9.65 |
| D1 | .315 | .350 | 8.00 | 8.89 |
| E | .380 | .410 | 9.65 | 10.41 |
| E1 | .245 | .320 | 6.22 | 8.13 |
| e | .100 BSC | 2.54 |  | BSC |
| L | .575 | .625 | 14.61 | 15.88 |
| L1 | .090 | .110 | 2.29 | 2.79 |
| L2 | .040 | .055 | 1.02 | 1.40 |
| L3 | .050 | .070 | 1.27 | 1.78 |
| L4 | 0 | .005 | 0 | 0.13 |

## TO-220 Outline


$\begin{array}{ll}\text { Pins: } & 1 \text { - Gate } 2 \text { - Drain } \\ & 3 \text {-Source }\end{array}$

| SYM | INCHES |  | MILLIMETERS |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | .170 | .190 | 4.32 | 4.83 |
| b | .025 | .040 | 0.64 | 1.02 |
| b1 | .045 | .065 | 1.15 | 1.65 |
| c | .014 | .022 | 0.35 | 0.56 |
| D | .580 | .630 | 14.73 | 16.00 |
| E | .390 | .420 | 9.91 |  |
| e | .100 |  | BSC | 10.66 |
| F | .045 | .055 | 1.14 | 1.40 |
| $H 1$ | .230 | .270 | 5.85 | 6.85 |
| $J 1$ | .090 | .110 | 2.29 | 2.79 |
| k | 0 | .015 | 0 | 0.38 |
| L | .500 | .550 | 12.70 | 13.97 |
| L1 | .110 | .230 | 2.79 | 5.84 |
| $\varnothing P$ | .139 | .161 | 3.53 | 4.08 |
| Q | .100 | .125 | 2.54 | 3.18 |

Figure 1. Output Characteristics at $25^{\circ} \mathrm{C}$


Figure 3. Output characteristics at $125^{\circ} \mathrm{C}$


Figure 5. $\mathrm{R}_{\mathrm{DS}(0 n)}$ normalized to $0.5 \mathrm{I}_{\mathrm{D} 25}$ value vs. $\mathrm{I}_{\mathrm{D}}$


Figure 2. Extended Output Characteristics at $125^{\circ} \mathrm{C}$


Figure 4. Admittance Curves


Figure 6. $\mathrm{R}_{\mathrm{DS}(\text { (on })}$ normalized to $0.5 \mathrm{I}_{\mathrm{D} 25}$ value vs. $\mathrm{T}_{\mathrm{J}}$


Figure 7. Gate Charge


Figure 9. Forward Voltage Drop of the Intrinsic Diode


Figure 11. Transient Thermal Resistance


Pulse Width - Seconds
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

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